

NTJD5121N, NVJD5121N

MOSFET – Power, Dual, N-Channel With ESD Protection, SC-88 60 V, 295 mA



ON Semiconductor®

Features

- Low $R_{DS(on)}$
- Low Gate Threshold
- Low Input Capacitance
- ESD Protected Gate
- NV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- This is a Pb-Free Device

Applications

- Low Side Load Switch
- DC-DC Converters (Buck and Boost Circuits)

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

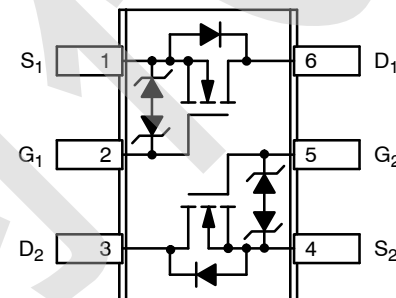
Parameter	Symbol	Value	Unit	
Drain-to-Source Voltage	V_{DSS}	60	V	
Gate-to-Source Voltage	V_{GS}	± 20	V	
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	295	mA
		$T_A = 85^\circ\text{C}$	212	
	$t \leq 5$ s	$T_A = 25^\circ\text{C}$	304	
		$T_A = 85^\circ\text{C}$	219	
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	250	mW
		$t \leq 5$ s	266	
Pulsed Drain Current	$t_p = 10$ μs	I_{DM}	900	mA
Operating Junction and Storage Temperature	T_J, T_{STG}	-55 to 150		$^\circ\text{C}$
Source Current (Body Diode)	I_S	210		mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260		$^\circ\text{C}$
Gate-Source ESD Rating (HBM)	ESD_{HBM}	2000		V
Gate-Source ESD Rating (MM)	ESD_{MM}	200		V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

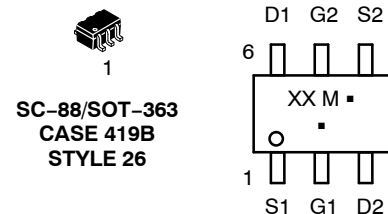
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D Max
60 V	1.6 Ω @ 10 V	295 mA
	2.5 Ω @ 4.5 V	

SC-88 (SOT-363)



Top View

MARKING DIAGRAM & PIN ASSIGNMENT



SC-88/SOT-363
CASE 419B
STYLE 26

XX = Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

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Parameter	Symbol	Value	Unit
Junction-to-Ambient – Steady State	$R_{\theta JA}$	467	°C/W
Junction-to-Ambient – $t \leq 5$ s	$R_{\theta JA}$	412	
Junction-to-Lead – Steady State	$R_{\theta JL}$	252	

1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J	I _D = 250 μA, ref to 25°C		92		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 60 V	T _J = 25°C		1.0	μA
			T _J = 125°C		500	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±10	μA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	1.0	1.7	2.5	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J			4.0		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 500 mA		1.0	1.6	Ω
		V _{GS} = 4.5 V, I _D = 200 mA		1.2	2.5	
Forward Transconductance	g _{FS}	V _{DS} = 5 V, I _D = 200 mA		80		S
Gate Resistance	R _G			536		Ω

CHARGES AND CAPACITANCES

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 20 V		26		pF
Output Capacitance	C _{OSS}		4.4			
Reverse Transfer Capacitance	C _{RSS}		2.5			
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 25 V, I _D = 200 mA		0.9		nC
Threshold Gate Charge	Q _{G(TH)}		0.2			
Gate-to-Source Charge	Q _{GS}		0.3			
Gate-to-Drain Charge	Q _{GD}		0.28			

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	t _{d(on)}	V _{GS} = 4.5 V, V _{DD} = 25 V, I _D = 200 mA, R _G = 25 Ω		22		ns
Rise Time	t _r		34			
Turn-Off Delay Time	t _{d(off)}		34			
Fall Time	t _f		32			

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 200 mA	T _J = 25°C		0.8	1.2	V
			T _J = 85°C		0.7		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

3. Switching characteristics are independent of operating junction temperatures.

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TYPICAL PERFORMANCE CURVES

($T_J = 25^\circ\text{C}$ unless otherwise noted)

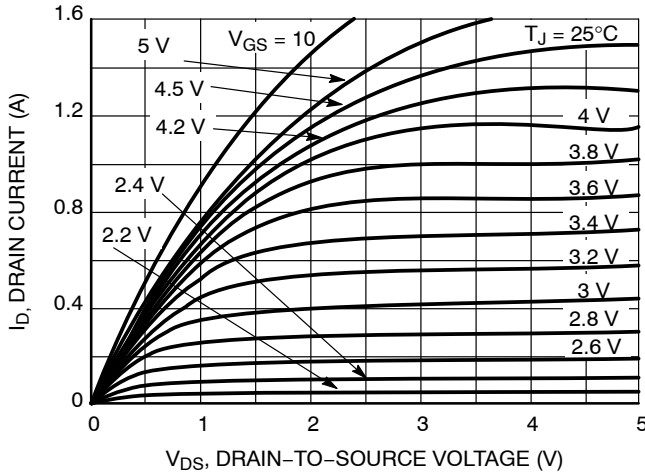


Figure 1. On-Region Characteristics

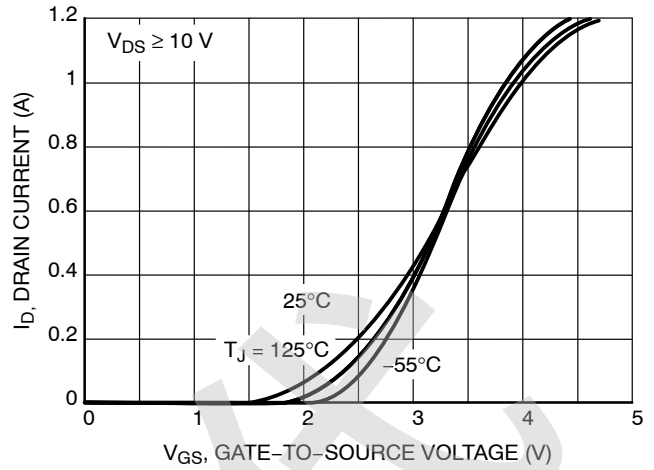


Figure 2. Transfer Characteristics

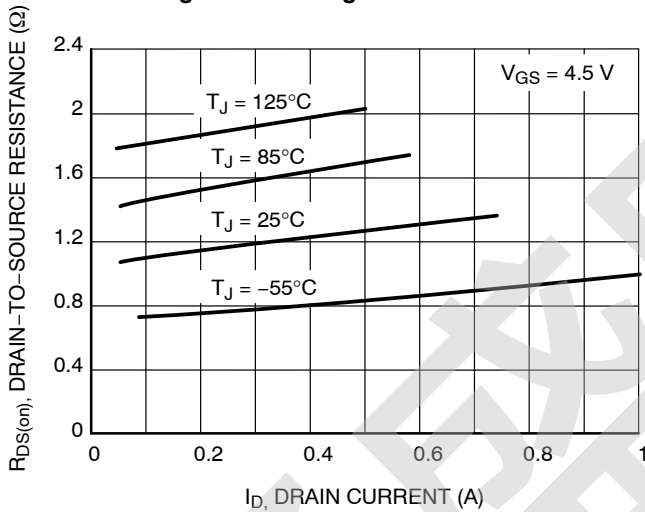


Figure 3. On-Resistance vs. Drain Current and Temperature

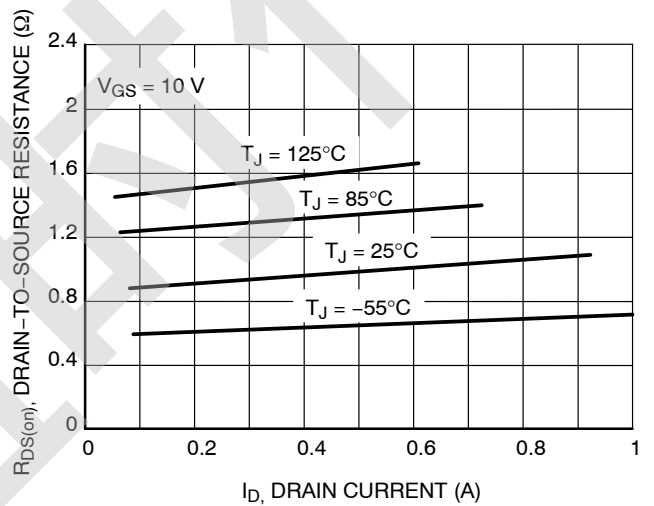


Figure 4. On-Resistance vs. Drain Current and Temperature

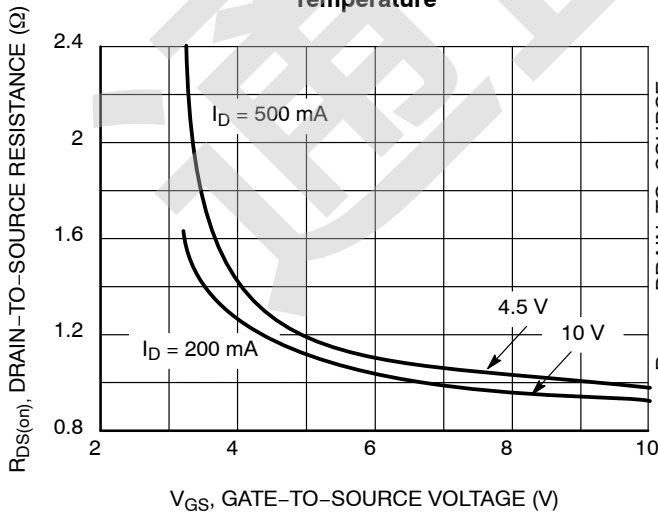


Figure 5. On-Resistance versus Gate-to-Source Voltage

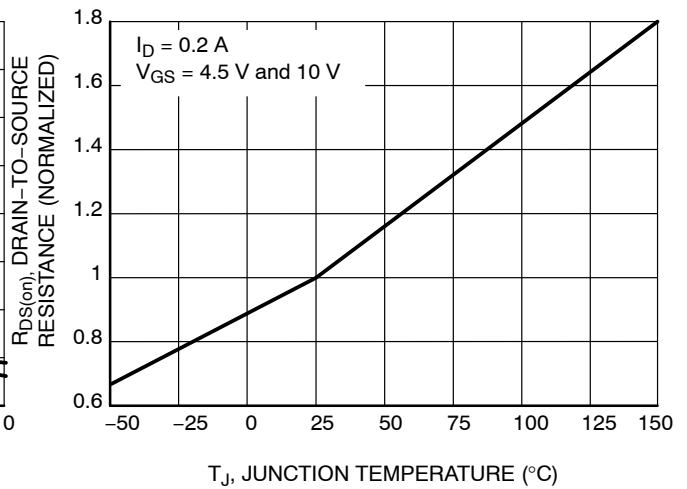


Figure 6. On-Resistance Variation with Temperature

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TYPICAL PERFORMANCE CURVES

($T_J = 25^\circ\text{C}$ unless otherwise noted)

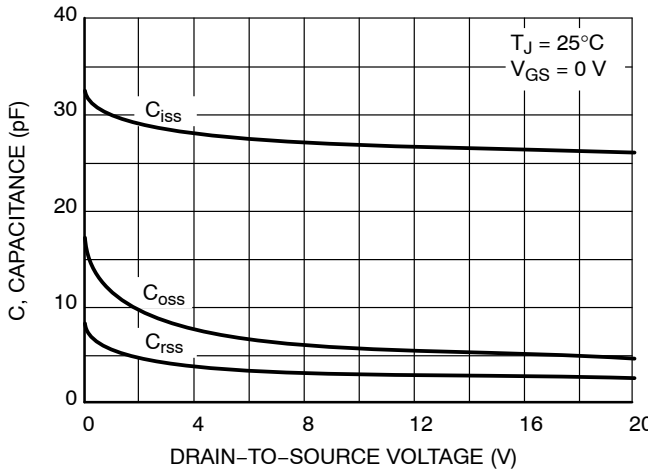


Figure 7. Capacitance Variation

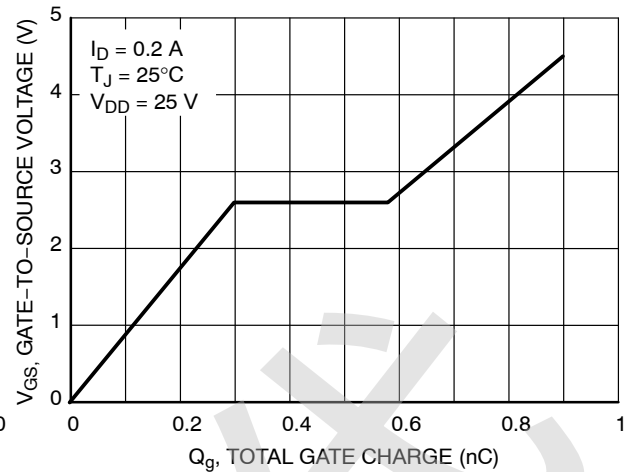


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

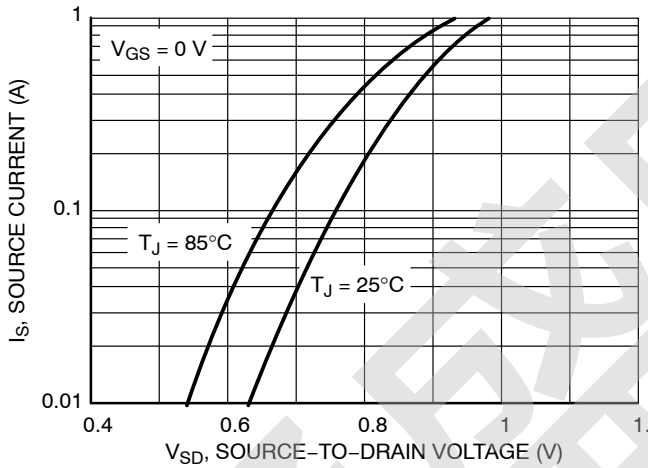


Figure 9. Diode Forward Voltage vs. Current

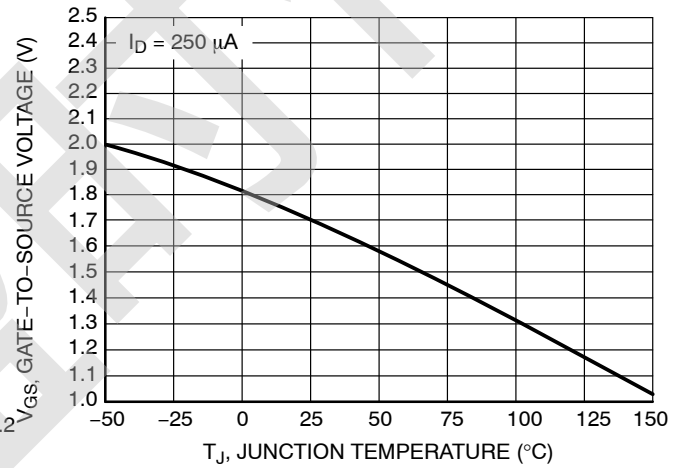


Figure 10. Threshold Voltage with Temperature

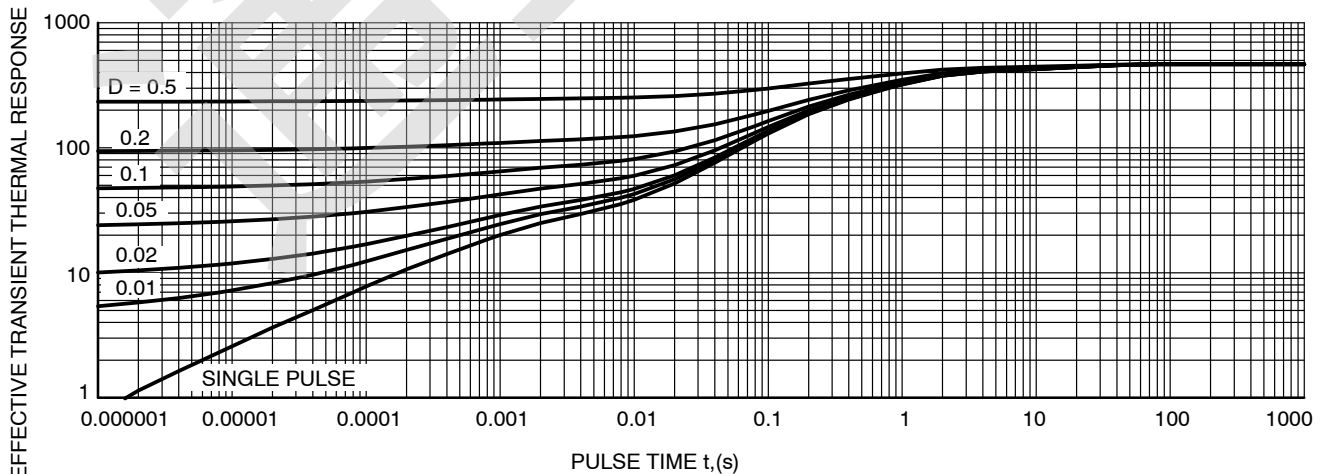


Figure 11. Thermal Response

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Table 1. ORDERING INFORMATION

Part Number	Marking (XX)	Package	Shipping [†]
NTJD5121NT1G	TF	SC-88 (Pb-Free)	3000 / Tape & Reel
NTJD5121NT2G	TF	SC-88 (Pb-Free)	3000 / Tape & Reel
NVJD5121NT1G	VTF	SC-88 (Pb-Free)	3000 / Tape & Reel

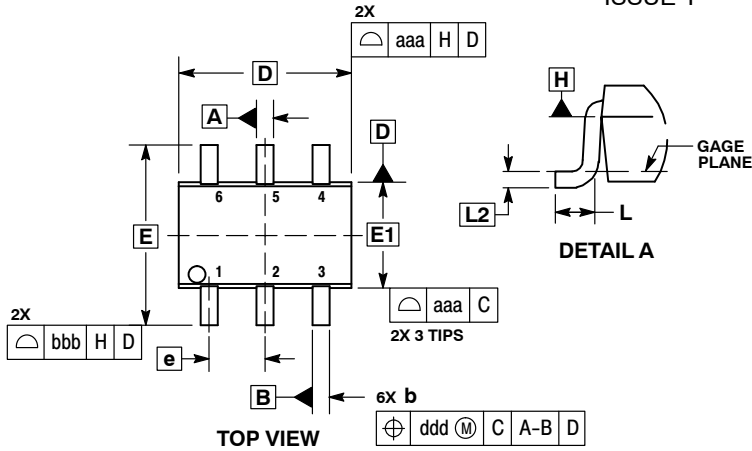
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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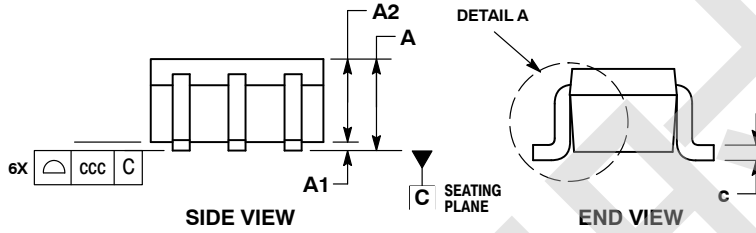
PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363
CASE 419B-02
ISSUE Y



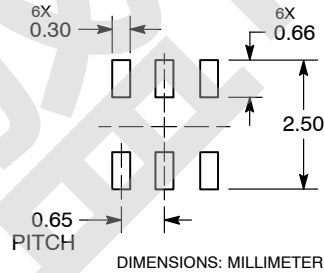
- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
 4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
 5. DATUMS A AND B ARE DETERMINED AT DATUM H.
 6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
 7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	---	---	1.10	---	---	0.043
A1	0.00	---	0.10	0.000	---	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10			0.004		



- STYLE 26:
1. SOURCE 1
 2. GATE 1
 3. DRAIN 2
 4. SOURCE 2
 5. GATE 2
 6. DRAIN 1

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.